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INVESTIGATION OF ADVANCED FAULT INSERTION AND SIMULATOR METHODS

FINAL TECHNICAL REPORT

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FINAL TECHNICAL REPORT

Report Summary

The cooperative agreement partly supported research leading to the open-literature publication cited below.

Additional efforts under the agreement included research into fault modelling of semiconductor devices. Results of this research are presented in this report which is summarized in the following paragraphs.

As a result of the cited research, it appears that semiconductor failure mechanism data is abundant but of little use in developing pin-level device models. Failure mode data on the other hand does exist but is too sparse to be of any (statistical) use in developing fault models. What is significant in the failure mode data is that, unlike classical logic, MSI and LSI devices do exhibit more than "stuck-at" and open/short failure modes. Specifically they are dominated by parametric failures and functional anomalies that can include intermittent faults and multiple-pin failures.

The report discusses methods of developing composite pinlevel models based on extrapolation of semiconductor device failure mechanisms, failure modes, results of (temperature) stress testing and functional modelling. Limitations of this model particularly with regard to determination of fault detection coverage and latency time measurement are discussed.

Indicated research directions are presented.

Reference

Dunn, W.R., "Software Reliability: Measures and Effects in Flight Critical Digital Avionics Systems", 7th Digital Avionics Systems Conference, Fort Worth, Texas, October 13-16, 1986.

Notation

DTL = Diode-Transistor Logic

FMEA = Failure Modes & Effects Analysis

FMET = Failure Modes & Effects Tests

LSTTL = Low Power Schottky Transistor-Transistor Logic

RAC = Reliability Analysis Center

SSI = Small Scale Integration

VLSI = Very Large Scale Integration

INVESTIGATION OF ADVANCED FAULT INSERTION AND SIMULATOR METHODS

1.0 Introduction

In the design and development of a flight-critical digital system, it is necessary to prove that the system can tolerate single- and multiple-component faults. Two widely-used methods supporting such proof are Failure Modes and Effects Analysis (FMEA) and Failure Modes and Effects Testing (FMET). FMEA is usually performed very early in the design process either by hand or, in more complex systems, through fault simulation. FMET is performed toward the end of development and prior to initial flight test. In Failure Modes and Effects Testing, actual or simulated faults are inserted in the actual digital system (generally configured in ground-based, "iron bird" environment) in order to validate system fault tolerance. Both FMEA and FMET activities require knowledge of probable component failure modes.

This report addresses the subject of digital integrated circuit semiconductor failure modes. The study leading to the report was motivated by the suspicion that the permanent, "stuck- at" type failure modes characteristic of relay, transistor and small-scale integrated circuit logic might not fully embrace possible failure modes in many of the Medium Scale Integration (MSI) and Very Large Scale Integration (VLSI) components employed in modern, flight-critical digital system designs. The study was therefore undertaken with the (admittedly ambitious) objective of developing an approach for deriving practical fault models for MSI digital integrated circuits. The work was subject to two important, practical constraints:

- 1) Owing to limited resources, detailed study would be confined to a limited number of Low Power Schottky Transistor-Transistor Logic (LSTTL) devices. (These devices are extensively employed in modern flight systems.)
- 2) The study would employ only that semiconductor reliability data available to the general public. (Superior data lies within the semiconductor houses but is, in general, not available to the avionics designer.)

As the informed reader might suspect, it was quickly determined that the latter reliability data was of very limited usefulness in terms of fault model development.*

^{*}At the time, workers at Hughes aircraft independently reached the same conclusion. See Reference 1.

For this reason, the originally-planned research activities were supplemented with laboratory stress testing of select LSTTL devices.

The remainder of this report is organized as discussed in the following.

Section 2.0 explains in detail what is meant by "fault model" and discusses past approaches to realizing fault models. Limitations of these models are discussed.

Section 3.0 presents definitions of semiconductor failure mechanisms and failure modes. Results of a USC survey and analysis of available failure mechanism and mode data bases are presented.

Section 4.0 describes several approaches to fault model development including use of semiconductor failure mode data and extrapolation of failure mechanism data. The section also contains a description of the test methodology and results of USC semiconductor stress testing.

Section 5.0 presents conclusions and indicated research directions.

2.0 Pin-Level Fault Modelling in Failure Modes and Effects Analysis and Testing

2.1 Pin Level Fault Model

Figure 2-1 shows the package outline of a general LSTTL device. In every device, two pins are dedicated to power supply source and return. The remaining pins are inputs and outputs. Under unfaulted conditions the device will output a predictable set of logic states (and/or state transitions) given a set of input states (and/or transitions) and (for sequential logic devices) a set of internal states. If there are failures internal to the device, output may be incorrect. To effect a pin-level fault model for the device, electrical characteristics at one or more pins are altered in such a manner that the resulting "new" device behaves exactly the same as the corresponding device with the internal failure.

In a FMEA these characteristics are introduced analytically. In a FMET, special circuitry is interposed between the good device and the system circuitry as shown in Figure 2-2 and altered characteristics are electrically introduced at the device pins. (Reference 2 & 3.)

This report focuses on approaches (and limitations) for determining these pin-level characteristics for failures that can occur within the device. (The term "fault modelling" is used in this report to describe this process.)

2.2 Gate-Level Fault Models

Prior to the introduction of integrated circuit logic (almost 30 years ago) it was relatively simple to correllate physical failures with the altered behavior of logic components. For example, the relay of Figure 2-3a could be associated with four fault characteristics: contact stuck-open, contact stuck-closed, coil short-circuited and coil open-circuited. Discrete component logic could be handled in a similar manner. For example, in the discrete component, diode-transistor-logic (DTL) gate of Figure 2-3b, one could directly associate known physical failures (open and shorted resistors, open diodes, collector-base opens, open solder joints, etc.) with behavior at the input/output terminals of the circuit.

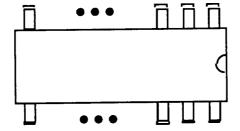


FIGURE 2-1 PACKAGE OUTLINE - LSTTL DEVICE

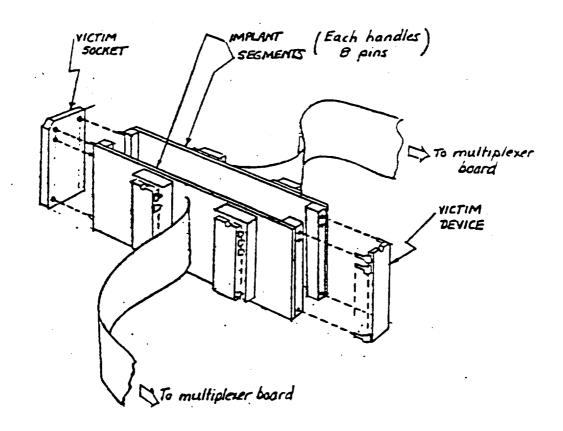
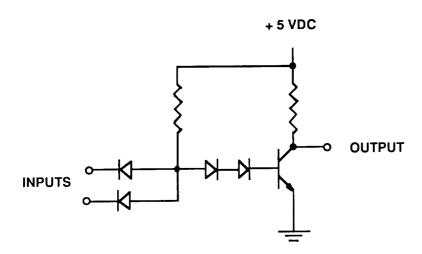


FIGURE 2-2 FAULT INSERTION CIRCUITRY



(a) Relay



(b) Discrete Diode-Transistor Logic
FIGURE 2-3 EARLY LOGIC DEVICES

The first digital integrated circuits consisted of single gates (such as the DTL gate of Figure 2-3b) implemented on a single chip. For reasons to be explained shortly (Section 3.3), on-chip physical failure mechanisms could not be translated to behavior at the output terminals. Instead, physical failures were considered in terms of altered behavior at the gate inputs and outputs which could be stuck-at-1, stuck-at-0, open-circuited or short-circuited. Realistic FMEAs and FMETs could be performed for early systems employing these small scale, integrated gates by successively applying each of these failure characteristics to each pin in the logic circuit.

2.3 Limitations of Gate-Level Fault Models

This report is concerned with fault modelling of commercial, non-custom MSI, LSI and VLSI digital semiconductor devices. (As noted, USC detailed studies were confined to LSTTL SSI and MSI devices. Findings with these specific devices appear however to apply to higher levels of integration and to other semiconductor technologies.) In attempting to apply classical, gate-level fault modelling to this class of devices, one encounters several practical roadblocks:

- 1) With a few exceptions, semiconductor manufacturers do not provide gate-level circuit schematics of their integrated devices. Consequently, one cannot perform a gate-level FMEA.
- 2) With early gate-level circuitry, it was possible to perform fault insertions (as a part of FMET) by opening and/or shorting gate inputs and outputs. In MSI and LSI, gates are integrated on the chip with the result that internal gate imputs and outputs cannot be physically accessed.
- 3) As will be seen in the next section, failure mechanisms within the device can lead to failure modes other than open-circuit, short-circuit and stuck-at behavior at the device pins.

3.0 Semiconductor Failure Mechanisms and Modes

3.1 Definitions

In what follows, the term <u>failure mechanism</u> refers to a physical anomaly within the device. <u>Failure mode</u> refers to altered electrical characteristics and/or behavior as a result of occurrence of the failure mechanism.

For example, a broken wire bond is a failure mechanism. It produces an open circuit failure mode at the pin to which it is connected.

3.2 Survey of Available Failure Mode and Failure Mechanism Data Bases

USC conducted a survey among some ten semiconductor manufacturers and three avionics firms in an effort to obtain failure mechanism and failure mode data to support pin-level fault modelling of select LSTTL devices. In the course of this survey, it was determined that these data are also collected by the DOD-sponsored Reliability Analysis Center (RAC) located at Griffiss AFB in New York.

Between the semiconductor manufacturers and the RAC, there is a copious amount of available data on digital semiconductor failure mechanisms. Failure mode data on the other hand is another matter. It is available only (with a few exceptions) from RAC which periodically publishes failure mechanism and failure mode data by semiconductor technology.

Tables 3-1 and 3-2 respectively summarize LSTTL failure mechanism and failure mode data taken from two RAC reports as referenced. Note that, in terms of the objectives of the study (to obtain pin level models of digital devices), these data represent the best* information gathered in the study.

3.3 Analysis of Failure Mechanism Data

With the exception of wirebond failures, it is virtually impossible to directly correlate semiconductor failure mechanisms with behavior at the device terminals. (Again, it is assumed that details of the chip circuitry and layout are not known.) The reason for this is that die defects (or package defects that lead to die contamination) can be very local (e.g. bad metal contact on a single emitter) or regional (e.g. an oxide contamination effecting several transistors). With each defect, the digital circuit structure can be altered. Given the range of possible combinations of defects one is inclined to speculate that a device could exhibit every possible combination of outputs for any given input (and input history in the case of a sequential circuit).

^{*}We had originally hoped to find failure mode data for each chip type. Unfortunately, (RAC) published data on each device type is too fragmentary to attach any statistical significance to the distribution of failure modes of any given device.

TABLE 3-1 - LSTTL Failure Mechanisms (SSI and MSI Devices)

1984 RAC Report (Ref. 4)

	ilure Mechanism y Component)	No. of Devices	
			Percentage
Die:		68	25.1
	Bulk Aspects	15	
	Metallization	38	
	Oxide/Dielectric	10	
	Surface	5	
Inte	rconnects:	24	8.8
	Wire	9	
	Wirebond	15	
Pack	age:	179	66.1
	Seal	116	
	Lid	54	
	Die Attach Bond	9	

TABLE 3-2 - LSTTL Device Failure Modes (Ref. 4) (SSI and MSI Devices)

Failure Mode	Percent <u>of Total</u>	Adjusted**
OPEN	3.4	3.4
SHORT	4.1	4.1
DEGRADED	22.4	22.4
Unknown*	3.4	0.0
Leakage	6.1	7.2
Parameter Out-of-Tolerance	12.9	15.2
FUNCTIONAL ANOMALY	70.1	70.1
Unknown	57.2	0.0
Non-Functional	2.7	14.8
Improper Output	9.5	51.6
Stuck-at-1	0.0	0.0
Stuck-at-0	0.7	3.7

^{*&}quot;Unknown" means failure mode was in major category (DE-GRADED or FUNCTIONAL ANOMALY) but sub-category (leakage, improper output, etc.) is not known.

^{**}Unknowns allocated to known categories in proportion to known percentages of total.

3.4 Analysis of Failure Mode Data

Unlike failure mechanism data, failure mode data (Table 3-2) describe faulted behavior at the device pins. What stands out most in the table is that the majority of failure modes in LSTTL are not the classical open, short and stuck- at modes but functional, parametric and leakage failures. (Table 3-3, prepared from the same RAC report, shows expectedly, that failure modes for the obsolescent DTL technology fall principally in the former category.)

Excess leakage and parameter out-of-tolerance failure modes could have three effects in an operational digital flight system:

- 1) If sufficiently severe, they could produce a hard or permanent device failure.
- 2) If borderline, they could produce a soft or intermittent device failure. (In working with LSTTL devices, one occasionally encounters what's called a "flaky chip": a device that works correctly most of the time but not always.)
- 3) If below fault-activating thresholds, the device could be expected to function properly but with reduced life.

It is observed that in both DTL and LSTTL implementations, leakage and parametic failures can constitute a significant portion of latent faults. Unlike the "stuck-bit" latent fault, leakage and parametric failure modes could conceivably be missed in preflight built-in-test yet become activated in the harsher environment of flight.

LSTTL failure mode data of Table 3-4 for both life test and field application would seem to indicate the presence of such latent faults in fielded equipment. It is important to qualify this latter statement as well as all of the RAC data related to LSTTL failure modes. Specifically the failure mode distributions of Table 3-2 correspond to a limited number of devices that does not span the full range of device types. Table 3-5 shows significantly different failure mode distributions for two separate LSTTL samples, one taken in 1984 (the data of Table 3-2) and another taken in 1980 (Reference 5). (As suggested by Table 3-6, this difference in distributions does not appear to apply to DTL.)

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TABLE 3-3 - DTL Failure Modes (Ref. 4)

Failure Mode	Percent of Total	Percent Adjusted**
OPEN	0.0	0.0
SHORT	6.2	6.2
DEGRADED	18.8	18.8
Unknown*	15.6	0.0
Leakage	1.6	9.4
Parameter Out-of-Tolerance	1.6	9.4
FUNCTIONAL ANOMALY	75.0	75.0
Unknown	46.9	0.0
Non-Functional	1.6	4.2
Improper Output	1.6	4.2
Stuck-at-1	10.8	29.1
Stuck-at-0	14.1	37.5

^{*&}quot;Unknown" means failure mode was in major category (DE-GRADED or FUNCTIONAL ANOMALY) but sub-category (leakage, improper output, etc.) is not known.

^{**}Unknowns allocated to known categories in proportion to known percentages of total.

TABLE 3-4 - LSTTL Device Failure Modes Life Test vs. Field

	Life Test	Field
Failure Mode	Percent of Total	Percent of Total
OPEN	3.5	4.5
SHORT	2.8	4.5
DEGRADED	22.4	10.7
FUNCTIONAL ANOMALY	71.3	80.3

TABLE 3-5 - LSTTL Device Failure Modes (SSI and MSI Devices)

Comparison of 1984 and 1980 Data

Failure Mode	Percent of Total 1984 Data (147 Devices)(4	Percent of Total 1980 Data 450 Devices)
OPEN	3.4	0.0
SHORT	4.1	0.4
DEGRADED	22.4	84.7
FUNCTIONAL ANOMALY	70.1	14.9

TABLE 3-6 - DTL Device Failure Modes

Comparison of 1984 and 1980 Data

Failure Mode	Percent of Total 1984 Data (64 Devices)	Percent of Total 1980 Data (59 Devices)
OPEN	0.0	0.0
SHORT	6.2	0.0
DEGRADED	18.8	20.3
FUNCTIONAL ANOMALY	75.0	77.7

4.0 Developing Pin-Level Device Models

4.1 Overview

Given the severe constraint that one does not "know" what's inside the semiconductor package, fault modelling becomes more art than science. This section, therefore, describes various approaches (employed by USC and others) which can be invoked collectively to develop a pin-level fault model. The approaches consist of device modelling based on,

- (1) failure mechanisms
- (2) failure mode data
- (3) device stress testing
- (4) functional modelling

4.2 Model Elements Based on Failure Mechanisms

4.2.1 Interconnects

Interconnect failure mechanisms consist of broken wire and detachment of die-pad and/or lead-frame wire bonds. These mechanisms can be modelled by:

- 1) introducing single (i.e. one-at-a-time) open-circuits at each pin.
- 2) introducing single short circuits across adjacent pins. (These two failure modes are also discussed in Section 4.3)

4.2.2 Die Defects/Package Failures

As discussed in Section 3.3, die defects and package failures can lead to a virtually infinite combination of incorrect signal outputs.

With SSI devices and (to a limited extent) MSI devices, all combinations could be considered (in FMEA) and inserted (in FMET) provided that circuit complexity is low. In complex circuits employing both MSI and LSI devices, such exhaustive testing is impractical. As a result one must consider altering outputs by randomly selecting a subset of total combinations or employing a set of "worst case" combinations based upon the specific circuit design.

4.3 Model Elements Based on Failure Mode Data

4.3.1 Open Circuits

Based on the 1984 RAC data, open circuits (pin- to-pad) constitute some 3% of total failure modes (Table 3-2). (Wire bond data in Table 3-1 tends to collaborate this fraction.) Note that open-circuit failure modes are single failures.

4.3.2 Short Circuits

Short circuits would include single shorts of adjacent pins.

4.3.3 Excess Leakage and Out-of-Tolerance Parameters

Note that failure mode data applies to leakages and parameters at the pins. We are of the belief that equivalent (for FMEA) or actual (for FMET) analog interface circuitry could be interposed between device pins and socket host to effect excess leakages and out- of-tolerance voltage levels, switching characteristics and delays. (This "parasitic circuit" model has, to date, not been pursued in the study.) Failure modes here would be single and multiple. With the same considerations discussed in Section 4.2.2, fault insertion testing involving all possible combinations of leakage currents and parameter values is not practical for complex circuitry. One would accordingly have to randomly select combinations or, where possible, select "worst case" combinations based on the design at hand.

4.3.4 Functional Anomalies

The non-functional chip, improper output and latched-output failure modes can be modelled using the classical "stuck-at" approaches. Again, one faces a virtually infinite number of fault combinations for MSI and LSI devices employed in complex circuitry.

4.4 Semiconductor Device Stress Testing

4.4.1 Rationale Behind Semiconductor Stress Testing

The failure modes termed "degraded" in Table 3-2 are the result of altered transistor gains, switching thresholds, changed (diffused) resistance values and excess leakage

current. (Responsible failure mechanisms would include marginal semiconductor doping concentrations and/or die bulk and surface contamination.) As seen in Table 4-1, these circuit parameters are all temperature dependent. Consequently by operating an LSTTL device outside of its specified operating temperature limits* it is possible to induce failure of the device.

4.4.2 Experimental Setup

USC students set up a high-temperature burn-in rig with which digital integrated circuits could be operated and monitored from room temperature up to 200 degrees Celsius.

Three LSTTL device types and one TTL device type were selected** for high temperature testing:

74LS138	1-of-8-DECODER/DEMULTIPLEXER
74174	HEX D-TYPE FLIP FLOPS
74LS257	QUAD 2-TO-1 MULTIPLEXER
74LS194	4-BIT SHIFT REGISTER

Burn-in circuits for these devices are shown in Figure 4-1.

4.4.3 Stress Testing Results

All devices tested were commercial components having a maximum operating temperature*** of 70 degrees Celsius.

The following describes results of operating the devices at elevated temperatures. (Device data sheets are presented in Appendix A.)

^{*}These limits define the temperature range over which the device manufacturer guarantees minimum and maximum parameter values.

^{**}These device types were concurrently being employed in fault insertion experiments at NASA Ames Research Center.

^{***}As noted earlier, this is the temperature beyond which the manufacturer will not guarantee minimum and maximum parameter values.

TABLE 4-1
Transistor Parameters vs. Temperature

		Typical	Values	
Parameter	<u>Units</u>	<u>-55 C</u>	25_C	<u>70_C</u>
Resistance (Diffused Resistor)	Ohms	320	360	450
(DC) Current Gain	dim.	65	100	200
LeakageCurrent	nA	10	70	300
Input Voltage Threshold	Volts	0.95	0.82	0.70

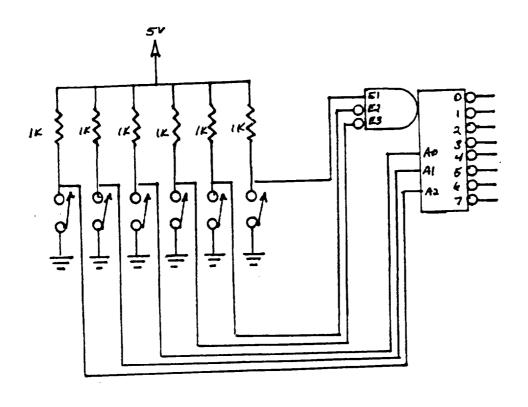


FIGURE 4-1a BURN-IN CIRCUIT FOR THE 74LS138

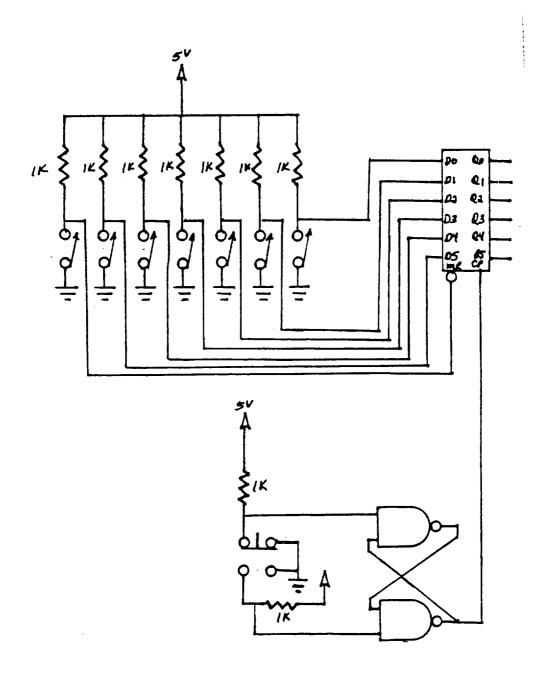


FIGURE 4-1b BURN-IN CIRCUIT FOR THE 74174

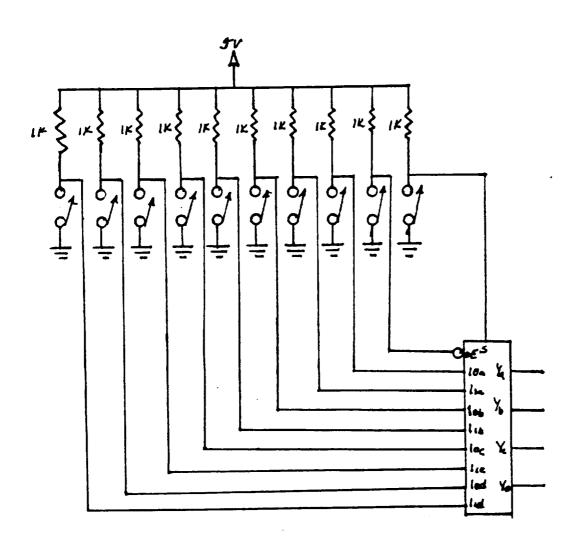


FIGURE 4-1c BURN-IN CIRCUIT FOR THE 74LS257

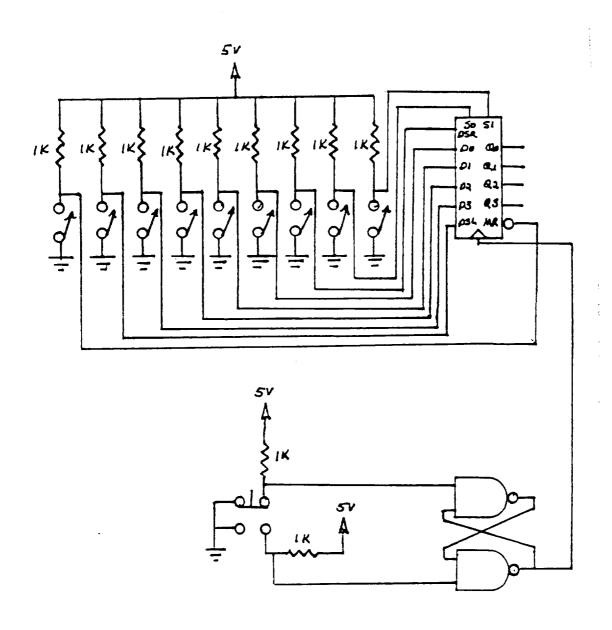


FIGURE 4-1d BURN-IN CIRCUIT FOR THE 74LS194

When testing the 74LS138, five different devices were tested under high temperature tests and the following results were obtained: In the first test, all of the outputs stuck high from 170 to 200 degrees Celsius. In the second test, all of the outputs stuck high from 170 to 200 degrees Celsius. For the other three tests, the circuits performed exactly as they were supposed to for temperatures from 20 to 200 degrees Celsius.

When testing the 74174, five different devices were tested and the following results were obtained: In the first test, output Q3 stuck low from 180 to 200 degrees Celsius. In the second test, the clock and output Q5 shorted together from 180 to 200 degrees Celsius. In the third test, output Q4 stuck high from 160 to 200 degrees Celsius. In the fourth test, all outputs stuck low from 100 to 200 degrees Celsius. In the fifth test, all outputs stuck low from 120 to 200 degrees Celsius.

When testing the 74LS257, five different devices were tested under high temperature tests and no change in the outputs was found from 20 to 200 degrees Celsius.

When testing the 74LS194, five different devices were tested under high temperature conditions and the following results were obtained: In the first test, outputs Q0, Q1, and Q2 were stuck high in the hold mode at 190 degrees Celsius. In the second test, all of the outputs stuck high at 200 degrees Celsius. In the third test, all of the outputs stuck high at 80 degrees Celsius. In the fourth test, all outputs were stuck high in the shift left mode at 200 degrees Celsius. In the fifth test, outputs Q1 and Q3 were stuck high in the parallel load mode from 80 to 200 degrees Celsius.

The foregoing test results are summarized in Table 4-2.

Appendix B shows the truth tables for each of the failed devices made at the time the device was failed. Note that all of the faults induced were permanent faults. (No attempt was made in the experiments to induce intermittent faults.)

TABLE 4-2
Semiconductor Device Stress Testing Results

DEVICE TYPE	DEVICE NO.	RESULTS
74LS138	1, 2	ALL OUTPUTS STUCKHIGH
	3, 4, 5	NO FAILURES
74174	1	Q3 STUCK LOW
	2	CLOCK AND Q5 SHORTED
	3	Q4 STUCK HIGH
	4, 5	ALL OUTPUTS STUCK LOW
74LS257	1, 2, 3, 4, 5	NO FAILURES
	1	Q0, Q1, Q2 STUCK HIGH
	2	ALL OUTPUTS STUCK HIGH
74LS194	3	ALL OUTPUTS STUCK HIGH
	4	ALL OUTPUTS STUCK HIGH (IN LEFT SHIFT MODE)
	5	Q1 AND Q3 STUCK HIGH (IN PARALLEL LOAD MODE)

4.5 Functional Fault Modelling

Given that gates in an LSI device are inaccessable (i.e. analytically in FMEA; physically in FMET), many workers have opted to employ functional models in performing fault free and fault insertion simulations (e.g. see References 6, 7 & Functional fault modelling, quite simply, consists of altering pin states (in simulation during FMEA; or in real time during FMET) such that the function of the (individual or sets of) pins is defeated. Table 4-3 shows functional faults for a select number* of LSTTL devices along with the corresponding alteration of pin states. Note that some of the fault insertions in the table require that pin states be changed instantaneously. (For example, the insertion "invert state" in Table 4-3a requires that the corresponding pin state must be monitored and changed.) While "instantaneous" changes are feasible in simulation, they may be impossible to achieve in physical fault insertion particularly where victim circuit speeds equal or exceed that of the insertion circuitry. Finally, it is noted that the fault insertions of Table 4-3 can occur as single or multiple faults and as well as being permanent or intermittent in duration.

4.6 Summary

As noted in the introduction to this section, a fault model for an LSTTL device would incorporate all of the approaches described above. These are summarized in Table 4-4 which also shows corresponding failure modes.

5.0 Conclusions and Indicated Research Directions

As a result of our investigations, we find that semiconductor failure mechanism data is abundant but of little use in developing pin level device models. Failure mode data on the other hand does exist but is too sparse to be of any (statistical) use in developing fault models.

What is significant in the failure mode data is that, unlike classical logic, MSI and LSI devices do exhibit more than "stuckat" and open/short failure modes. Specifically they are dominated by parametric failures and functional anomalies that can include intermittent faults and multiple pin failures.

^{*}These device types were concurrently being employed in fault insertion experiments at NASA Ames Research Center.

TABLE 4-3a FUNCTIONAL FAULT MODELLING
2901 MICROPROCESSOR SLICE

FUNCTIONAL FAULT INSERTION	PIN	FAULT
Register select failure (A port)	4 (AO)	invert state
**	3 (A1)	ıı
11	2 (A2)	11
11	1 (A3)	11
Register select failure (B port)	17 (BO)	11
n	18 (B1)	н
п	19 (B2)	11
n	20 (B3)	11
Microinstruction decode fail	12 (I0)	11
п	13 (I1)	TI TI
п	14 (I2)	u
и	26 (I3)	u
n	28 (14)	11
tt	27 (I5)	tt
ti .	5 (16)	"
ti	7 (17)	н
ti .	6 (18)	***
Correct data shift fail (Q req.)	8	open
п	9	***

TABLE 4-3a FUNCTIONAL FAULT MODELLING
2901 MICROPROCESSOR SLICE

(CONTINUED)

FUNCTIONAL FAULT INSERTION	PIN	FAULT
Correct (Y) output fail state	36	invert
п	37	11
п	38	11
ti .	39	11
Output disable*	40	S-a-1
Carry generate/prop fail state	32	invert
n .	35	11
Overflow (false) fail	34	S-a-1
ALU zero (false) fail	11	S-a-1
ALU MSB out fail state	31	invert
Carry-in fail	29	S-a-1
Clock fail	15	S-a-1
п	15	S-a-0

^{*}Tied low on all 2901 chips.

TABLE 4-3b Functional Fault Modelling
2911 Microprogram Sequencer

FUNCTIONAL FAULT INSERTION	PIN	FAULT
Address source select fail state	10	invert
н	11	Ħ
Push/pop stock oper. fail	19	tt
n	20	tī
Internal reg. select fail	3	S-a-1
Zero enable fail	9 (zero)	S-a-1
Zero disable fail	9	S-a-0
Y-enable fail	16	S-a-1
Y-disable fail	16	S-a-0
Incrementer carry-in fail	17	S-a-0
Ħ	6	invert state

TABLE 4-3c Functional Fault Modelling
2918 Quad D Register

FUNCTIONAL FAULT INSERTION	PIN	FAULT
Y enable fail	7 (OE)	S-a-1
Y disable fail	7 (OE)	S-a-0
Clock fail	9 (CP)	S-a-0
Correct Q output fail	2 (Q0)	invert state
11	5 (Q1)	tt.
ιτ	11 (Q2)	11
τι	14 (Q3)	11
CorrectY output fail	3 (YO)	invert state (when pin $7 = 0$)
ιτ	6 (Y1)	и
π	10 (Y2)	u
11	13 (Y3)	"

TABLE 4-3d Functional Fault Modelling

54LS253 Dual 4-Input Multiplexer

FUNCTIONAL FAULT INSERTION	PIN	FAULT
Chip enable fail	1 (Mux 1 enable)	S-a-1
11	15 (Mux 2 enable)	tt
Chip disable fail	1	S-a-0
11	15	11
Channel select fail state	14 (select 0)	invert
11	2 (select 1)	TT TT
Correctoutput fail	7 (Mux 1 out)	invert when pin 1 = 0
и	9 (Mux 2 out)	invert when pin 15 = 0

TABLE 4-3e Functional Fault Modelling
54LS02 - Quad NOR

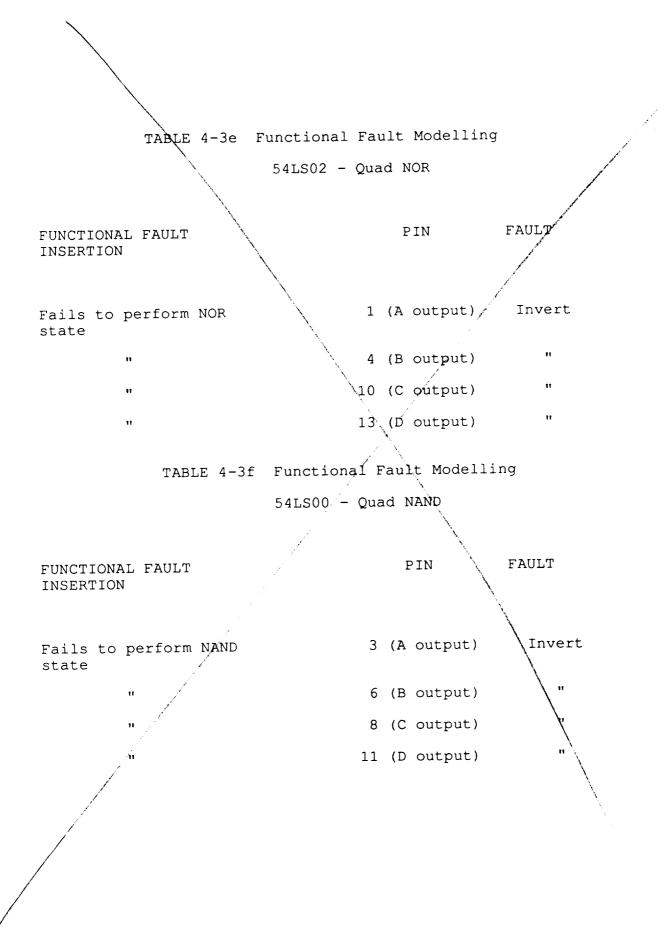
FUNCTIONAL FAULT INSERTION		PIN	FAULT
Fails to perform NOR state	1	(A output)	Invert
Ħ	4	(B output)	tt
11	10	(C output)	***
tt	13	(D output)	n

TABLE 4-3f Functional Fault Modelling
54LS00 - Quad NAND

FUNCTIONAL FAULT INSERTION		PIN	FAULT
Fails to perform NAND state	3	(A output)	Invert
11	6	(B output)	II
tt	8	(C output)	tt
11	11	(D output)	tt

TABLE 4-3g Functional Fault Modelling
5404 Hex Inverter

FUNCTIONAL FAULT INSERTION		PIN	FAULT
Fails to invert state	1	(A input)	Invert
н	3	(B input)	tt
н	5	(C input)	tt
п	9	(D input)	11
н	11	(E input)	11
п	13	(F input)	11



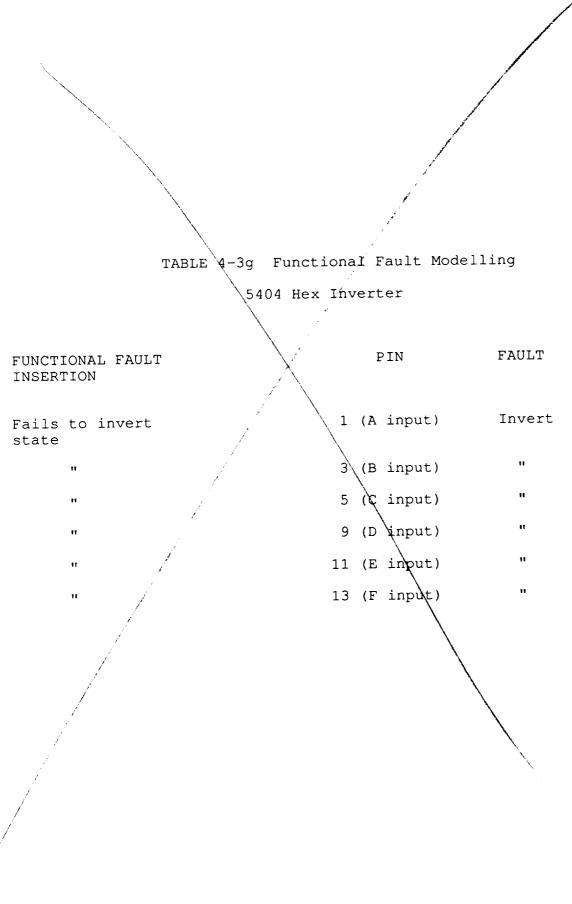


TABLE 4-4 - LSTTL Failure Modes and Fault Models

Failure Mode Fault Model

Functional Anomaly Functional Fault Model

(FMEA); Model Generated

Fault Patterns (FMET)

Degraded (At Pins) Parasitic Circuit

Degraded (On Chip)

Device Stress Tests to

Corroborate Functional

Fault Model

Opens Open-Circuit Pin

Shorts Short-Circuit Adjacent

Pins

It is certainly possible, and this report discusses the methods, to develop pin-level models based on extrapolation of semiconductor device failure mechanisms, failure modes, results of (temperature) stress testing and functional modelling. Such a composite model would include credible faults that could be experienced by the device. Unfortunately, the number of such faults would be insignificant when compared to the (virtually infinite) number of possible fault patterns. At issue here is the fact that one could insert all the faults in a composite model and yet gain no accurate measure of fault detection coverage and/or fault latency times. I.e. one could demonstrate fault tolerance yet come away with no measures of the degree of fault tolerance.

The foregoing prompt several research questions:

- 1) Although single-pin "stuck-at" or open/short permanent fault insertions do not characterize the modern MSI and LSI device, can they be legitimately* employed to cover actual failure modes that might be experienced?
- 2) Is it possible to obtain a definition of coverage and coverage measures with a device which can exhibit permanent or intermittent failures at one or more device pins?
- 3) Is one better off considering failure patterns at electrical connection boundaries other than integrated circuit pins (e.g. data busses, I/O lines, etc.)?

^{*}The approach is extensively used today with FMEA.

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Acknowledgements

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APPENDIX A DEVICE DATA SHEETS

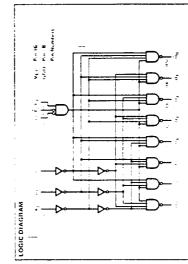
M MOTOROLA

DESCRIPTION — The LSTIL MSI SNS-11S 74(S138)s a high speed 1 of 8 Deceder "Demulpiture" This divice is dishiply stricted in high speed bipolar memory chip sidect address decoding. The multide input enables along weak-life tensors in to a 1 of 24 the colong. The multide input in the LS138 devices or to a 1 of 32 decoder using four LS138 and one merrer. The LS138 is tabricated with the Schottly bruner dinde process forms speed and is completely compatible with all Minisorial TIL samiles.

- DEMULTIPLEXING CAPABILITY
 MULTIPLE INDUT ENABLE FOR EASY EXPANSION
 TYPICAL POWER DISSIPATION OF 32 mW
 ACTIVE LOW MULTUALLY EXCLUSIVE OUTPUTS
 INPUT CLAMP DIODES LIMIT HIGH SPEED TERMINATION
 FFECTS

	DING.	0.25 U.L		105201
	104	1050		1001
2		Addres s leptors	Foable (Active LOW) Injust:	Active LOVY (bulgads (Note b)
	PIN NAMES	A 0 = 42	E1 F2	00 - 07

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3.1.5

9999999 HC1 S 1

4 9

J Suffee Cave 620 OB (Ceraenic) N Suffee - Case 648 05 (Paster)

MOTOROLA SCHOTTKY LEL DEVICTS

A-1

Decoder

1-of-8

54LS138

SN54LS138 SN74LS138

FUNCTIONAL DESCRIPTION — The LS138 is a high great Lot 8 Dicoster/Demolraphese Talmeated with the law power Scholiky barrier diode process. The elecuter accepts three timery weekfact reports (Ag. Ag. Ag.) and when enabled process eight minutely exclusive active. COW outputs (Ag.) A The LS138 features these Eachlet enpairs, two across to and one across HEGH Egg. All outputs will be HEGH unless E.; and Eg. are LOW and Egg. HEGH Egg. All outputs will be HEGH unless E; and Eg. are LOW and Egg. HEGH.

The LS138 can be used as an 8 output demutiplese by using one of the actor LOW Evalue inputs as the data report and the data report and the final temperature and the defendence as studies. The Evalue inputs which are not used must be permanently risel to their appropriate actors HOM or active LOW state.

decoder with just from LS138s and one inverter. (See Figure a.)

10

16

0

TRUTH TABLE

1-OF-8-DECODER/ DEMULTIPLEXER LOW POWER SCHOTTKY LOGIC SYMBOL

CONNECTION DIAGRAM
DIP (TOP VIEW) VCC - P.II 16 GVD - P.A 8

H - HIGH Voltage Level | - LOW Voltage Level | X - Dunit Care

MOSE.
The Statest persons has the same general of the merchan it separal as the Dustin tending age.

MOTOROLA SCHOTTKY TTL DEVICES

TYPES SN54174, SN54175, SN54LS174, SN54LS175, SN54S174, SN54S175, SN74174, SN74175, SN74LS174, SN74LS175, SN54LS175, SN54

BULLETIN NO DES 7511803 DECEMBER 1972-REVISED OCTOBER 1976

'174, 'LS174, 'S174 . . . HEX D-TYPE FLIP-FLOPS
'175, 'LS175, 'S175 . . . QUADRUPLE D-TYPE FLIP-FLOPS

- 174, 'LS174, 'S174 Contain Six Flip-Flops with Single-Rail Outputs
- '175, 'LS175, 'S175 Contain Four Flip-Flops with Double-Rail Outputs
- Three Performance Ranges Offered: See Table Lower Right
- Buffered Clock and Direct Clear Inputs
- Individual Data Input to Each Flip-Flop
- Applications include:

 Buffer/Storage Registers
 Shift Registers

 Pattern Generators

description

These monolithic, positive-edge-triggered flip-flops utilize TTL circuitry to implement D-type flip-flop logic. All have a direct clear input, and the '175, 'LS175, and 'S175 feature complementary outputs from each flip-flops.

Information at the D inputs meeting the setup time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock input is at either the high or low level, the D input signal has no effect at the output.

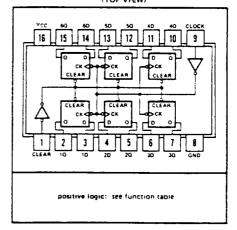
These circuits are fully compatible for use with most TTL or DTL circuits.

FUNCTION TABLE

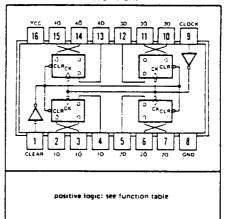
(EACH FLIP-FLOP)				
INPUTS OUTPL			PUTS	
CLEAR CLOCK D			Q	ā٢
L	X	×	L	H
н	;	н	н	L
н	•	L	L	н.
н	L	X	a _o	$\bar{\mathbf{q}}_{0}$

- H = high level (steady state)
- $L^{-\alpha}$ low level (steady state)
- X = (rrelevant
- = transition from low to high level
- ûg the level of Q before the indicated steady-state
 - input conditions were established.
- * * 175, 'LS175, and 'S175 only

SN54174, SN54LS174, SN54S174 . . . J OR W PACKAGE SN74174, SN74LS174, SN74S174 . . . J OR N PACKAGE (TOP VIEW)



SN54175, SN54LS175, SN54S175 . . . J OR W PACKAGE SN74175, SN74LS175, SN74S175 . . . J OR N PACKAGE ITOP VIEWI



	TYPICAL	TYPICAL
TYPES	MAXIMUM	POWER
11763	CLOCK	DISSIPATION
	FREQUENCY	PER FLIP-FLOP
1174, 1175	35 MHz	38 mW
'LS174, 'LS175	40 MHz	14 mW
'S174, 'S175	110 MHz	75 mW

TEXAS INSTRUMENTS
INCORPORATED
POST OFFICE BOX 5012 - DALLAS, TEXAS 75222

7-253

M MOTOROLA

DESCRIPTION — The LSTIL/MSI SN64LS/74LS257A and the SN64LS/74LS258A are Ound 2 frough Multiplears; with 3 state outputs Four bits of date from two sources can be selected using a Common Data Select input. The four outputs present the elected data in true (non-inverted) for the outputs present the elected data impedance state with a HiGH on the common Output Enable (EQHipput, allowing the outputs to increate directly with but connected systems is a fabricated with the Schotity barrier diodepocess to high shall be completely compatable with all Motorola TIL families.

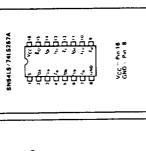
- SCHOTTKY PROCESS FOR HIGH SPEED
 MULTIPLEXER EXPANSION BY TYING OUTPUTS TOGETHER
 NON-HIVERTING 3-STATE OUTPUTS
 HIRPLT CLAMP DIODES LIMIT HIGH SPEED TERMINATION
 EFFECTS

LOGIC DIAGRAMS SN5418/7415267A

CONNECTION DIAGRAM DIP (TOP VIEW)

LOW POWER SCHOTTKY

QUAD 2-INPUT MULTIPLEXER WITH 3-STATE OUTPUTS



SN541 S. 741 S258A

J Suffix - Case 620 08 (Ceramic) N Suffix -- Case 648 05 (Plastic) WOTE The Happak version has the seme penduck (Connection Diegram) as the Duel In Line Perhage

VCC - Pin 16 GND - Pin 8 O - Pin Numbris

4-236

MOTOROLA SCHOTTKY TTL DEVICES

SN54LS/74LS257A SN54LS/74LS258A

FUNCTIONAL DESCRIPTION — The LS251A and LS258A are Duad 2 inout Multipleares with 3 state outputs. They select four bits of data from two sources select from 10 of a common Data Selection. When this Select frou its CDW, the 40 inous are selected and when Select is HIGH, the 11 mouts are selected and an the selected inputs are selected and selected inputs as a speasars at the outputs in true from inverted) form for the LS251A and in the inverted form for the LS258A.

The LS287A and LS288A are the logic implementation of a 4-pole. 2 position switch where the position of the switch is determined by the logic levels supplied to the Sefect Input. The logic equations for the outputs are shown below.

 $Z_b = \overline{e}_O \bullet (1_1b \bullet S + 1_0b \bullet \overline{S})$ $Z_d = \overline{e}_O \bullet (1_1d \bullet S + 1_0d \bullet \overline{S})$ $Z_b = \overline{E}_0 \circ (1_1 \circ \circ S + t_{0a} \circ \overline{S})$ $Z_c = E_0 \circ (1_1 \circ \circ S + t_{0c} \circ \overline{S})$ LS267A LS258A

 $\widetilde{Z}_{b} = \widetilde{E}_{0} \circ (1_{1b} \circ S + l_{0b} \circ \widetilde{S})$ $\widetilde{Z}_{d} = \widetilde{E}_{0} \circ (1_{1d} \circ S + l_{0d} \circ \widetilde{S})$ $\vec{Z}_{c} = \vec{E}_{O} \cdot (11_{O} \cdot S + 10_{O} \cdot \vec{S})$ $\vec{Z}_{c} = \vec{E}_{O} \cdot (11_{C} \cdot S + 10_{C} \cdot \vec{S})$ When the Output Enable Input (EQ) is HIGH, the outputs are forced to a high impedance "off" state if the outputs are ited together, all but one device must be in the high impedance state to avoid high currents that would acceed the measurem raings. Designers should ensure that Output Enable signals to 3 state devices whose outputs are teld together are designed so there is no overlap.

CT DATA OUTPUTS OUTPUTS UT INPUTS LS267A LS268A	Z Z 1, 0,	(Z) (Z) X X	×	×	×	ı ×
SELECT DA	O _l	×	×	_		
OUTPUT	E 0	I		_	_	_

H = HGH Voltage Level
L = LOW Voltage Level
R = Don't Cave
G] = High impedence (off)

GUARANTE	0 0 PERM					H
SYMBOL	PARAMETER		Z	ΤγP	MAX	į,
	Superpose	54	4.5	50	5.5	
23.	form fiding	7	4 75	20	5 75	
	Our man Anthon Towns alue Rance	54	55	72	125	
<u> </u>		74	0	25	0	
	Outras Current - High	\$			-10	
5		7			26	
1	Orders Custom - I may	54			13	
ಕ	Carlos carros - Carlos	7.			74	
						ı

> 0 4 4 4

MOTOROLA SCHOTTKY TTL DEVICES

4.237

Multiplexer 2-Input Quad

54LS257

A-3

FUNCTIONAL DESCRIPTION — The Logic Diagram and Truth Table indicate the functional characteristics of the LS194A 4 Bit Bidirectional Shift Register. The LS194A is similar in operation to the Motorola LS195A Universal Shift Register when used in serial or parallel data register transfers. Some of the common features of the two devices.

are described below:

All data and mode control inputs are edge tragered, responding only to the LOW to HIGH transition of the Clock (CP).
 The advis training estimation, therefore, a that the mode control and selected data inputs must be stable one as up time prior to the positive stantistion of the clock pulse.

The register is fully synchronous, with all operations taking place in less than 15 ns (typical) making the device especially useful for implementing very high speed CPUs, or the memory buffer registers 3. The low publish data inputs $\{P_0, P_1, P_2, P_3\}$ are Disperingon. When both S_0 and S_1 are HiGH, the data appraints P_0, P_1, P_2 , and P_3 inputs at transferred to the Q_0, Q_1, Q_2 , and Q_3 outputs respectively following the next LOW to HIGH insulton of the clock. The asynchronous Master Reset (MR), when LOW, overrides all other input conditions and forces the Q outputs LOW

M MOTOROLA

SN54LS194A SN74LS194A

DESCRIPTION — The SNS4LS/74LS194A is a High Spead 4 Bin Bedrectional Universal Shift Register As high speed multilunctional sequential building block, it is useful in a wide variety of applications It may be used in serial-serial, shift felt, shift right, serial-parallet, parallet-serial-speater transfers The LS194A is similar in operation to the LS195A Universal Shift Register, with added features of thill telt without external connections and hold (do nothing) modes of operation It utilises the Scholity diode clamped process to achieve high speeds and is fully compatible with all Motorole IT Lamines.

- TYPICAL SHIFT FREQUENCY OF 38 MHz
 ASYNCHRONOUS MASTER RESET
 HOLD (IOO NOTHING) MODE
 FULLY SYNCHRONOUS SERIAL OR PARALLEL DATA
 TRANSFERS
 INDUT CLAMP DIODES LIMIT HIGH SPEED TERMINATION

4-BIT BIDIRECTIONAL UNIVERSAL SHIFT REGISTER LOW POWER SCHOTTKY

CONNECTION DIAGRAM DIP (TOP VIEW)	J Suffix — Case 620 08 (Ceramic) N Suffix — Case 648 O5 (Plasix)

HIGH LOW 05 U. 0 25 U.

0.25 U L 0.25 U L 0.25 U L 0.25 U L 5(2.5) U L 0.25 U.L.

1050 OSUL. 1050 OSUL

> Clock (Active HIGH Going Edge) Input Master Retet (Active LOW) Input Serial (Shift Right) Data Input Sevial (Shift Left) Data Input

Qo - Qg Parallel Outputs (Note b)

CONNECTION DIAGRAM DIP (TOP VIEW)	00000000000000000000000000000000000000	J Suffia — Case 620-08 (Ceramic) N Suffia — Case 648 OS (Plasic)

Notice of the bad of the late of the bad of	
lay (54) and 5 U. to Commercel	
NOTES. 1 ITTURAL LONG LONG DAY NIGHTI & MAILEY (54) and \$ U.L. for Commerced in the Object COM days become a 1 \$ U.L. for Mailey (54) and \$ U.L. for Commerced in 134) Temperature Names.	VCC = Pm 18 VCC =

Two mode control inputs 15_0 , 5_1) determine the synchronous operation of the device. As shown in the Mode Selection Table, data can be entered and shirted from the first only the first 0_1^{-1} , 0_2^{-1} , 0_3^{-1} , 0_3^{-1} , 0_3^{-1} , 0_3^{-1} , 0_3^{-1} , 0_3^{-1} , 0_3^{-1} , and the selected loading all four bits of the respirite numbinarously. When both 5_0 and 5_1 are LOW, the satisfied data is retained in a "50 nothing" mode without estiticting the HIGH to LOW clock transition.

Special logic features of the LS194A design which increase the range of application are described below

D type serial data inputs IDSR, DSL) are provided on both the first and last stages to allow multistage shift right or thirt left data stansfers without interfering with parallel foad operation:

MODE SELECT - TRUTH TABLE

L - LOW Vollage tevel
H- Hilds Vollage tevel
T- LOW sollage between setting times prior to the LOW to HIGH coach treation
T- LOW sollage between setting times prior to the LOW to HIGH coach treation
T- LOW sollage prior to set top time prior to the LOW to HIGH coach treation
De (B.) Lower cess times and care the time of the referenced input for buildful coach times to find prior to the _ | | | | | | | | | | | Paraner Load

Shift Hight Shilt Lett

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OUTPUTS

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DSL

DSR.

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OPERATING MODE

Rese

MOTOROLA SCHOTTKY TTL DEVICES

4.193

Register Shift Universal Bidirectional 4-Bit 54LS194

A-4

PIN NAMES 50. S1 DSA

MOTOROLA SCHOTTKY TTL DEVICES

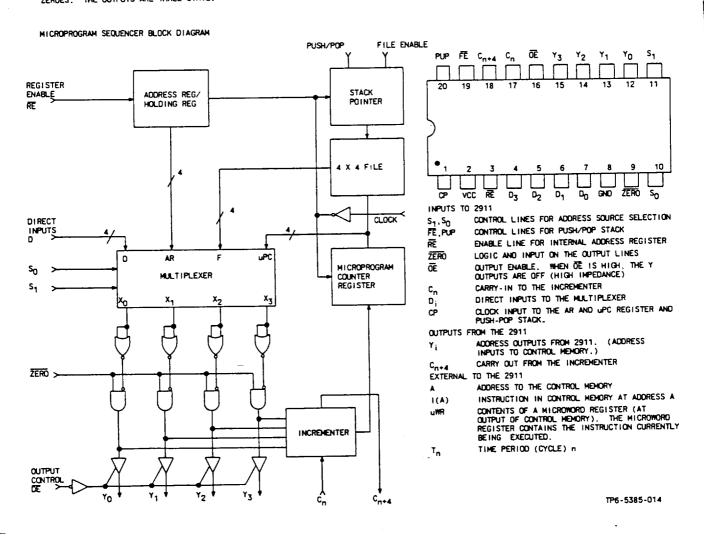
4-192

Mode Control Inputs Parallel Data Inputs

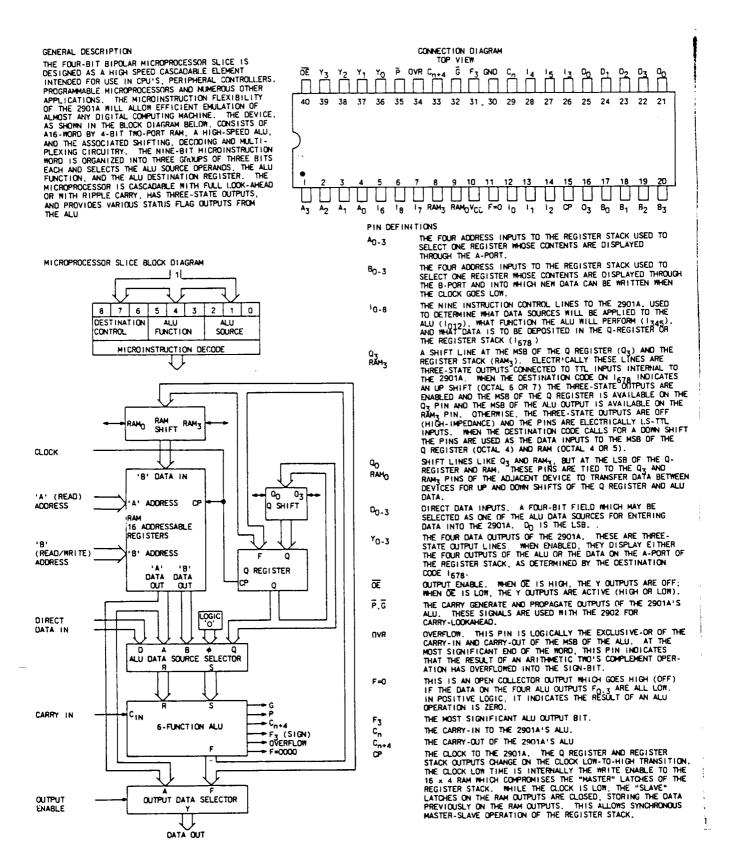
GENERAL DESCRIPTION

THE 2911 IS A FOUT-BIT WIDE ADDRESS CONTROLLER INTENDED FOR SEQUENCING THROUGH A SERIES OF MICROINSTRUCTIONS CONTAINED IN A ROM OR PROM. TWO 2911'S MAY BE INTERCONNECTED TO GENERATE AN EIGHT-BIT ADDRESS (256 WORDS), AND THREE MAY BE USED TO GENERATE A TWELVE-BIT ADDRESS (4K WORDS).

THE 2911 CAN SELECT AN ADDRESS FROM ANY OF THREE SOURCES. THEY ARE: 1) A SET OF EXTERNAL DIRECT INPUTS (0): 2) A FOUR-WORD DEEP PUSH/POP STACK: OR 3) A PROGRAM COUNTER REGISTER (WHICH USUALLY CONTAINS THE LAST ADDRESS PLUS ONE). THE PUSH/POP STACK INCLUDES PUSH/POP STACK: OR 3) A PROGRAM COUNTER REGISTER (WHICH USUALLY CONTAINS THE LAST ADDRESS PLUS ONE). THE PUSH/POP STACK INCLUDES CERTAIN CONTROL LINES SO THAT IT CAN EFFICIENTLY EXECUTE NESTED SUBROUTINE LINKAGES. A SEPARATE LINE FORCES THE OUTPUTS TO ALL ZEROES. THE OUTPUTS ARE THREE-STATE.



4-Bit Controller Type 2911

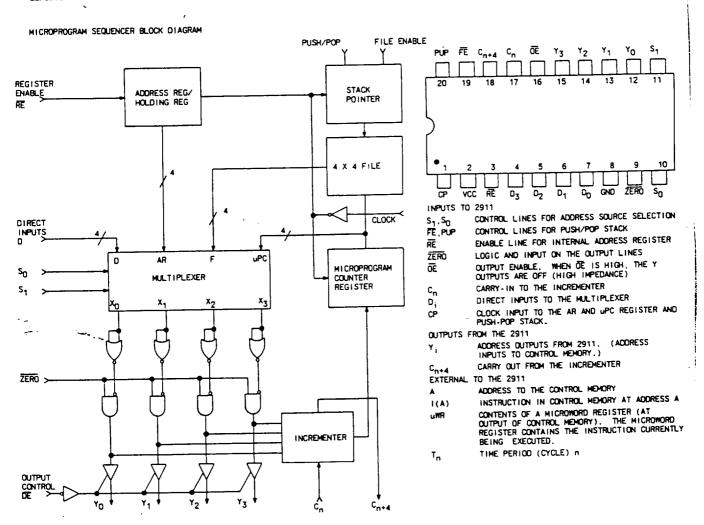


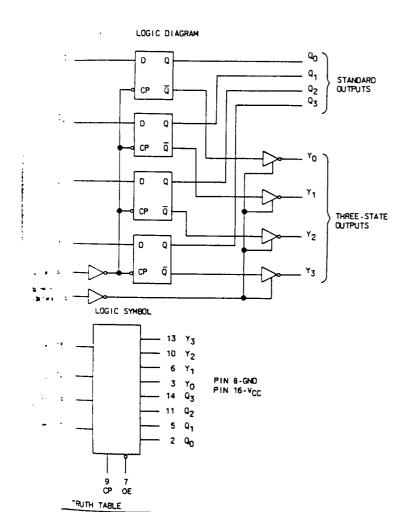
2901 Microprocessor Slice

GENERAL DESCRIPTION

THE 2911 IS A FOUT-BIT WIDE ADDRESS CONTROLLER INTENDED FOR SEQUENCING THROUGH A SERIES OF MICROINSTRUCTIONS CONTAINED IN A ROM OR PROM. TWO 2911'S MAY BE INTERCONNECTED TO GENERATE AN EIGHT-BIT ADDRESS (256 WORDS), AND THREE MAY BE USED TO GENERATE A TWELVE-BIT ADDRESS (4K WORDS).

THE 2911 CAN SELECT AN ADDRESS FROM ANY OF THREE SOURCES. THEY ARE: 1) A SET OF EXTERNAL DIRECT INPUTS (D): 2) A FOUR-WORD DEEP PUSH/POP STACK; OR 3) A PROGRAM COUNTER REGISTER (WHICH USUALLY CONTAINS THE LAST ADDRESS PLUS ONE). THE PUSH/POP STACK INCLUDES PUSH/POP STACK; OR 3) A PROGRAM COUNTER REGISTER (WHICH USUALLY CONTAINS THE LAST ADDRESS PLUS ONE). THE PUSH/POP STACK INCLUDES CERTAIN CONTROL LINES SO THAT IT CAN EFFICIENTLY EXECUTE NESTED SUBROUTINE LINKAGES. A SEPARATE LINE FORCES THE OUTPUTS TO ALL ZEROES. THE OUTPUTS ARE THREE-STATE.





DESCRIPTION

THE 2918 CONSISTS OF FOUR D-TYPE FLIP-FLOPS WITH A BUFFERED COMMON CLOCK. INFORMATION MEETING THE SET-UP AND HOLD REQUIREMENTS ON THE D INPUTS IS TRANSFERRED TO THE Q OUTPUTS ON THE LOW-TO-HIGH TRANSITION OF THE CLOCK.

THE SAME DATA AS ON THE Q OUTPUTS IS ENABLED AT THE THREE-STATE Y DUTPUTS WHEN THE "OUTPUT CONTROL" (QE) INPUT IS LOW. WHEN THE QE INPUT IS HIGH, THE Y OUTPUTS ARE IN THE HIGH-IMPEDANCE STATE.

THE 2918 IS A 4-BIT, HIGH-SPEED REGISTER INTENDED FOR USE IN REAL-TIME SIGNAL PROCESSING SYSTEMS WHERE THE STANDARD OUT-PUTS ARE USED IN A RECURSIVE ALGORITHM AND THE THREE-STATE OUTPUTS PROVIDE ACCESS TO A DATA BUS TO DUMP THE RESULTS AFTER A NUMBER OF ITERATIONS.

THE DEVICE CAN ALSO BE USED AS AN ADDRESS REGISTER OR STATUS REGISTER IN COMPUTERS OR COMPUTER PERIPHERALS.

THE 2918 IS ALSO USEFUL IN CERTAIN DISPLAY APPLICATIONS WHERE THE STANDARD OUTPUTS CAN BE DECODED TO DRIVE LED'S (OR EQUIVALENT) AND THE THREE-STATE OUTPUTS ARE BUS ORGANIZED FOR OCCASIONAL INTERROGATION OF THE DATA AS DISPLAYED.

DEFINITION OF FUNCTIONAL TERMS

- O; THE FOUR DATA INPUTS TO THE REGISTER.
- Q. THE FOUR DATA OUTPUTS OF THE REGISTER WITH STANDARD TOTEM-POLE ACTIVE PULL-UP OUTPUTS. DATA IS PASSED NON-
- Y; THE FOUR THREE-STATE DATA OUTPUTS OF THE REGISTER. WHEN THE THREE-STATE OUTPUTS ARE ENABLED. DATA IS PASSED NON-INVERTED. A HIGH ON THE "OUTPUT CONTROL" INPUT FORCES THE Y; OUTPUTS TO THE HIGH. IMPEDANCE STATE.
- CP CLOCK. THE BUFFERED COMMON CLOCK FOR THE REGISTER ENTERS DATA ON THE LOW-TO-HIGH TRANSITION.
- OE OUTPUT CONTROL. WHEN THE QE INPUT IS HIGH, THE YI OUTPUTS ARE IN THE HIGH-IMPEDANCE STATE. WHEN THE QE INPUT IS LOW, THE TRUE REGISTER DATA IS PRESENT AT THE

	uts	OUTP		INPUTS	
NOTES	Y	Q	D	CLOCK	ĴĒ
-	Z	NC NC	×	L	#
:	Z	L-	Ĺ	7	H
:	Z L	H	H	;	Ĺ
١.	н	lн	н	1 + 1	L

L

L

L = LOW H = HIGH NC = NO CHANGE

X = DON'T CARE

= LOW TO HIGH TRANSITION Z = HIGH IMPEDANCE

NOTE:

WHEN OF IS LOW. THE Y OUTPUT WILL BE IN THE SAME LOGIC STATE AS THE Q OUTPUT.



MOTOROLA

DESCRIPTION — The LSTT. MSI SNS4LS/74LS253 is a Dual 4-fround Miniputer with 3 state outpoint it forms sherithebase didatation four sources using common select inputs. The outpoint may be individually worther to infer impensive state with a HGF4 outpoint respective Output is nable (6) insulant allowing pine outputs or ontextue directly with bus oncerted systems. It is fabricated with the Schottity burner added process for high speed and is completely comparable with all Morrisola TIL Jamiles.

DUAL 4-INPUT MULTIPLEXER WITH 3-STATE OUTPUTS

LOW POWER SCHOTTKY

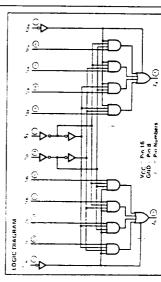
- SCHOTTAY PROCESS FOR HIGH SPEED
 MULTIFUNCTION CAPABILITY
 NON-INVERTING 3-STATE OUTPUTS
 INPUT CLAMP DIODES LIMIT HIGH SPEED TERMINATION
 FFECTS

LOGIC SYMBOL LOADING (Note 3)

	нОн	
Common Select Inputs	1040	02501
Output Enable (Active LOW) Input	05 UL	02501
Multiplexer Inputs	0501	0.25 U.L
Multiplexer Output (Note b)	65(25) U.L	1015781
Output Enable (Active LOW) Input	0501	0.25 U.L
Multiplexer Inputs	0501	02501
Mutiplexer Output (Note b)	65(25) U.L	1517 51 U.L

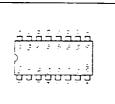
So St Multiplexer A PIN NAMES

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2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	CONNECTION DIAGRAM DIP (TUP VILV)	- - - - - - - - - - - - - - - - - - -



J Suffer Case 620 OB (Ceramic) N Suffer Cover 648 OS (Peramic) NOTE

For Couples serving has the same
proof of onesting Disposed as mafollower the Package

·

FUNCTIONAL DESCRIPTION — The LSS53 contains two identical 4 Input Moltplexet with 3 state output. They ω two bits from four sources setected by common select inputs (δ_0, δ_1) . The 4-input moltplexets have individual ω_{ω_1} . Enable (δ_0, δ_0) inputs which when HIGH, forces the outputs to a high imperfance (high, δ_1 state.

SN54LS253 SN74LS253

The LSSS3 is the logic implementation of a 2 pole, 4 position switch, where the position of the switch is determined to a logic feets supplied to the two select inputs. The logic equations for the outputs are shown person.

 $z_{t}, \epsilon_{01}, \epsilon_{02}, \epsilon_{13}, s_{1}, s_{2}, \epsilon_{13}, s_{1}, s_{2}, \epsilon_{13}, s_{1}, s_{2}, s_{2})$ $Z_{\underline{a}} \stackrel{E}{\leftarrow} E_{0\underline{a}} \cdot (1_{0\underline{a}} \cdot \overline{S}_{1} \cdot \overline{S}_{0} + 1_{1\underline{a}} \cdot \overline{S}_{1} \cdot S_{0} + 1_{2} \cdot S_{1} \cdot \overline{S}_{0} + 1_{33} \cdot S_{1} \cdot S_{0})$

If the outbus of 3 state devices are field together, all find one device must be in the high impedance state to are counterfits that would exceed the maximum rations. Devices should entire in the Operation and exceed the maximum rations. Devices should entire in the operation are the disperted to that there is no overlay.

3 2	SELEUT CPUTS		4140	DATA INPUT		CHITPLE E	OUTPUT
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	PROM LP. A				i i		
	1000 1000						
-	Interestation						

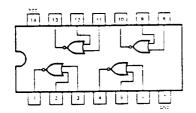
GUARANTEED OPERATING RANGES SMORE

FAMANTE IL

50,	J Southern Venter		
	story area for the early form and a story form		
#.	Value of more than		
ಕ	Triest Available 10.5	 	

4-Input Multiplexer Dual 54LS253





J Suffix — Case 632-07 (Ceramic) N Suffix — Case 646-05 (Plastic)

SN54LS02 SN74LS02

QUAD 2-INPUT NOR GATE

LOW POWER SCHOTTKY

GUARANTEED OPERATING RANGES

	PARAMETER		MIN	TYP	MAX	UNIT
SYMBOL	PARAMETER		107111		-	
VCC .	Supply Voltage	5 ÷	4.5	5.0	5.5	V
		7.4	4 75	5.0	5 25	<u>. </u>
TA	Operating Ambient Temperature Range	54	-55	25	125	1°C
- ^	-	7.4	0	25	70	i
¹ ОН	Output Current — High	54.74			-04	mA
IOL	Output Current — Low	54		i	4.0	mé
·OL	Compar Comment	7:		1	8.0	į.

DC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (unless otherwise specified)

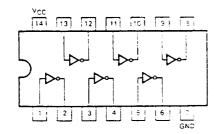
			-	LIMITS		UNITS	TEST CONDITIONS
SYMBOL	PARAMETER		MIN	TYP.	MAX	UNITS	TEST CONDITIONS
V _{IH}	Input HIGH Voltage		2.0	-	!	٧	Guaranteed Input HIGH Voltage for All Inputs
		54			0 -		Guaranteed Input LOW Voltage for
VIL	Input LOW Voltage	7.	-		Çá	V	1 All Inputs
Vitr	Input Clamp Dioge Voitage	2e	1	-0.65	- 1.5	V.	VCC = MIN. IIN = -18 m4
		5.4	2.5	3.5		V	VCC = MIN. IOH = MAX. VIN = VIH
ΛCri	Output HIGH Voltage =	7.:	2 -	3 €		•	or Vit per Truth Table
		54 74		J 2 (- IOL = 40 mA VCC = VCC MIT.
VO1	Output LOW Voltage 7	7.2		0.37	∴ €	У	Per Truth Table
					2 ::	lies	V _{CC} = MAX, V _{IN} = 2.7 /
hн	Hinput HIGH Current				2:	mΑ	V _{CC} = MAX, V _{IN} = 7.0 V
IIL.	Input LOW Current				0 -	m#	VCC = MAX VIN = 04 V
los	Short Circuit Current		7.7		-101	me	VCC = MAX
icc	: Power Supply Current				<u> </u>	m Ä	Ver = MAX

AC CHARACTERISTICS: $T_A = 25$ °C

		LINTE		UNITS		TEST CONDITIONS
SYMBOL	PARAMETER	Min The	MAX	· UKITS		TEST CONDITIONS
telH	Turn Off Delay, Input to Output	1.5	15	ns	,	VCC = 50 V
1PHL	Turn On Delay, Input to Output		15	ns		Ct = 15 pF

54LS02 Quad Nor





J Suffix — Case 632-07 (Ceramic) N Suffix — Case 646-05 (Plastic)

SN54LS04 SN74LS04

HEX INVERTER

LOW POWER SCHOTTKY

GUARANTEED OPERATING RANGES

SYMBOL	PARAMETER		MIN	TYP	MAX	UNIT
Vcc	Supply Voltage	5. 1 74	4 5 4 75	5.0 5.0	5.5 5.25	! v
TA	Operating Ambient Temperature Range	54 74	-55 0	25 25	125 70	^C
Юн	Output Current — High	54 . 74			-04	mA
OL	Output Current — Low	5∸ 74			4 0 8 C	mA

DC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE juniess otherwise specified)

				LIMITS		UNITS	TEST CONDITIONS	
SYMBOL	PARAMETER		MIN	TYP	MAX	UNITS	1231 C	UNDITIONS
VIH	· input HIGH Voltage		2.0			V	Guaranteed Inp	ur HIGH Vortage for
		54			0.7			ut LOW Voltage for
V _{IL}	Input LOW Voltage	74	•		0.5	V	All Inputs	
Vik	Input Clamp Diode Voita	ice		-0.65	-: 5	7	VCC = MIN. lin	= -18 mA
	Output HIGH Voltage	54	2 b	3.5				H = MAX. VIP) = VIE
л Он	Output High Voltage	7.4	2 7	3.5			or VIL per Truth	Table
-		54.74		0.26	3.4	V		Voc = Voc Mit.
vc-	Output LOW Voltage	7.		0.38	0 E	V	10L = 8.0 mA	T Viji = Viji or Vik j per Truth Table
					2.7	1,5	VCC = MAX. V	rg = 2.7 V
l ₍	input HIGH Current				:	m-i	VCC = MAX. V	inj = 7 0 %
-1	Input LOW Current				î -	mA	1 Vcc = MAX. V	N = 04
'CS	Snort Circuit Current		-21		-100	nı∴	V _{CC} = MAX	
les	Fower Supply Current Total, Output HIGH Total, Output LOW				2.4	- má	VCC = MAX	

AC CHARACTERISTICS: TA = 2510

	0.0.445770	1	LIMITS		UNITS		TEST CONDITIONS
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	!	TEST CONDITIONS
tPLH	Turn Off Delay, Input to Output		9.0	15	ns		V _{CC} = 5.0 V
TPHL	Turn On Delay, input to Output		10	15	ns		C _L = 15 pF

5404 Hex Inverter

APPENDIX B TEMPERATURE STRESS TEST RESULTS

7	H	H	H	H	H	H	H	H	Ħ	H	П
9	н	ж	н	Н	Ħ	Ħ	Н	Ħ	н	H	H
5	Н	н	н	н	Н	Ħ	н	н	IJ	н	н
4	Ħ	Н	Ħ	田	н	Н	Н	ч	н	H	Н
κ	н	H	H	Н	Н	Н	н	Н	H	н	щ
2	Н	H	H	Н	H	Ţ	H	н	Н	н	н
~ 1	н	н	н	Н	ij	Н	ij	н	ш	Н	H
0	Н	н	Н	IJ	н	н	Н	н	н	н	H
E3	×	×	ī	щ	н	н	н	н	Ħ	н	Н
E2	×	н	×	ы	ы	H	Ħ	H	ı	П	L
E 1	н	×	×	п	П	ы	н	ч	IJ	ы	ы
A2	×	×	×	П	ı	ы	ᆸ	н	ж	Ħ	н
A1	×	×	×	ı	П	н	ц	ц	H	Н	Н
A0	×	×	×	П	Ħ	ı	ц	ы	н	IJ	Н

L = LOW VOLTAGE LEVEL

H = HIGH VOLTAGE LEVEL

X = DON'T CARE

74LS138 (Device No. 1) @ 170 C

7	н	Ж	н	н	Н	щ	H	н	н	H	н
9	ж	Ħ	H	H	H	н	н	н	Н	H	Н
2	Ħ	Ħ	H	н	Н	щ	н	Н	н	Н	н
4	Н	Ħ	Н	Н	н	н	田	H	Н	H	н
κ	H	Н	н	Н	Н	н	Н	н	н	H	н
2	н	Ħ	Н	Н	Н	н	Н	н	н	Н	н
7	Ħ	н	Н	н	H	Н	Н	Н	Н	н	н
0	Ħ	н	н	н	Н	H	Н	н	н	Н	н
E3	×	×	ı	н	н	н	н	н	н	н	ж
E2	×	н	×	Ţ	ı	H	н	ы	н	ı	IJ
E1	Ħ	×	×	ᆸ	IJ	Н	щ	I	ъ	IJ	П
A2	×	×	×	П	T	ı	H	Н	Н	н	н
Al	×	×	×	IJ	ц	нн	ᆸ	П	H	н	н
A0	×	×	×	H	H	μн	ī	IJ	Ħ	ц	н

B-2

H = HIGH VOLTAGE LEVEL

X = DON'T CARE

74LS138 (Device No. 2) @ 170 C

7	н	н	н	н	Н	н	Н	Н	Н	H	Н
9	H	щ	Ħ	Н	田	н	Ħ	H	Н	н	田
2	н	н	н	щ	щ	H	H	H	ж	н	Н
4	н	Ħ	H	н	田	H	H	Н	н	Ħ	Н
т	Н	Н	н	Н	Н	н	н	н	н	Н	Н
2	Ħ	Н	н	н	H	Н	Н	Н	н	H	н
٦	Н	щ	Н	Н	Н	н	н	н	н	Н	Н
0	Ħ	н	щ	н	н	Н	H	н	н	Ħ	H
E3	×	×	ы	н	н	н	н	н	н	н	Н
E2	×	н	×	П	П	1	Н	ı	ı	T	T
E 1	Н	×	×	ы	П	H	Н	H	ы	ŭ	ы
A2	×	×	×	H	ᆸ	ı	ы	н	н	н	н
Al	×	×	×	П	н	Н	ı	IJ	ı	Н	н
A0	×	×	×	ы	Н	ц	디	I	Н	ı	н

X = DON'T CARE

H = HIGH VOLTAGE LEVEL

05	Ы	IJ	田
04	ы	П	·H
03	ы	ц	н
02	ы	ı	н
<u>0</u> 1	ы	ı	н
00	Н	Ц	н
D5	×	Н	出
D4	×	IJ	H
D3	×	H	н
D2	×	H	Н
D1	×	ı	н
D0	×	П	н
MR	Н	н	Ħ
CP	×	4	4

@ 180 C

74174

04	IJ	H	H
60	Ы	T	Н
92	ы	ı	н
01	Ы	IJ	Ξ
00	ı	Ы	н
D2	×	T	н
D4	×	ы	Н
D3	×	Ц	H
D2	×	ы	н
D1	×	IJ	Н
D0	×	IJ	н
MR	П	н	H
CP	×	4	4

05

П

 Ξ

X = DON'T CARE

↑ = POSTIVE GOING CLOCK PULSE

H = HIGH VOLTAGE LEVEL

05	ы	IJ	H
04	П	H	Ħ
60	ı	ы	н
02	ᄓ	Ţ	н
01	IJ	Ţ	Н
00	ы	IJ	щ
D2	×	ī	ш
D4	×	IJ	щ
D3	×	IJ	н
D2	×	ı	н
D1	×	н	H
00	×	ы	н
MR	니	Н	н
CP	×	←	←

74174 (Device No. 4) @ 120 C

Q5 L	П	니
04 L	ы	ı
1 1	IJ	ij
02 L	IJ	IJ
21 L	IJ	П
D0	Г	IJ
D5 X	IJ	Н
D4 X	Ы	Н
X X	Ц	н
D2 X	П	H
D1 X	H	Н
00 x	IJ	H
MR L	Н	H
X CP	←	4

X = DON'T CARE

↑ = POSTIVE GOING CLOCK PULSE

H = HIGH VOLTAGE LEVEL

T 02	ᆸ	Н
04 1	Ļ	Ц
03 L	Ļ	Ы
02 L	IJ	H
01 L	니	ы
001	IJ	ы
D5	ij	н
D4 X	IJ	Ħ
х D	Ц	Ħ
D2 X	Ц	Ħ
D1 X	IJ	Ħ
0 X	П	Ħ
L M	Н	Ħ
X X	←	6 -

74LS257 @ 25 C (No Failure)

Н	Г	H	П	田
YD		Ħ		
$_{\rm L}^{\rm YC}$	П		H	Н
YE				
YA L	Ţ	Ħ	IJ	H
IID	П	H	×	×
I1C X	IJ	Ħ	×	×
I1B X	긔	Ħ	×	×
IIA X	니	H	×	×
IOD X	×	×	н	Н
IOC	×	×	ы	H
IOB	×	×	Н	Н
IOA X	×	×	Ц	н
s ×	H	н	ı	IJ
OE H	H	니	Н	ᆸ

X = DON'T CARE

T = POSTIVE GOING CLOCK PULSE

H = HIGH VOLTAGE LEVEL

H	IJ	H	T	Η	H	H	田
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ᆔ	Ц	ы	н	н	H	Н	H
IJ	J	ы	IJ	Н	IJ	H	Н
×	H	H	н	П	IJ	н	H
×	IJ	ı	H	H	Н	н	Ħ
×	×	H	ī	×	×	×	×
×	×	×	×	×	×	IJ	H
×	×	×	×	×	×	П	H
×	×	×	×	×	×	ч	Н
×	×	×	×	×	×	ы	н
×	×	×	×	出	П	×	×
ı	H	н	н	н	H	Н	Н
×	←	←	←	←	4	4	←
	L X X X X X L L L	L X X X X X X L L L L L L L L L L L L L	L X X X X X L	1 1	L X X X X X Y	1. X X X X Y	1 X X X X Y

L = LOW VOLTAGE LEVEL

↑ = POSTIVE GOING CLOCK PULSE

X = DON'T CARE

H = HIGH VOLTAGE LEVEL

03	н	П	H	Н	Ħ	П	ы	Н
02	ц	H	니	Ħ	н	ı	T	H
01	ı	H	Ħ	H	工	Ы	Ц	H
00	T	Ħ	н	н	Н	ı	ы	н
S1	×	ı	H	H	H	ı	Ħ	Н
20	×	H	IJ	H	Н	Н	щ	Н
DSL	×	×	н	IJ	×	×	×	×
D3	×	×	×	×	×	×	IJ	H
D2	×	×	×	×	×	×	П	н
D1	×	×	×	×	×	×	Ц	н
DO	×	×	×	×	×	×	IJ	Н
DSR	×	×	×	×	Ħ	ы	×	×
MR	IJ	н	H	н	н	н	н	H
CP	×	←	4	←	←	←	←	←

X = DON'T CARE

= POSTIVE GOING CLOCK PULSE

HIGH VOLTAGE LEVEL || |H

田

CP	×	←	4	←	←	←	←	←
MR	П	Ħ	H	Ħ	Ħ	Н	H	Η
DSR	×	×	×	×	Ħ	ы	×	×
DO	×	×	×	×	×	×	г	Н
D1	×	×	×	×	×	×	IJ	H
D2	×	×	×	×	×	×	ᆸ	H
D3	×	×	×	×	×	×	ı	H
DSL	×	×	Ή	ı	×	×	×	×
20	×	ij	П	ы	Ħ	H	H	Ξ
S1	×	Ц	H	H	П	IJ	田	Ξ
00	ы	H	Ħ	H	Ħ	H	Ħ	Ξ
01	н	н	Ħ	Н	茁	Ħ	H	Ξ
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X = DON'T CARE

↑ = POSTIVE GOING CLOCK PULSE

H = HIGH VOLTAGE LEVEL

 $\boldsymbol{\Xi}$

工

 \blacksquare

 \mathbb{H}

 \mathbb{H}

 \mathbb{H}

 \mathbb{H}

= DON'T CARE ×

= POSTIVE GOING CLOCK PULSE

HIGH VOLTAGE LEVEL II

Η

03	н	Γ	H	田	Ħ	Ħ	П	Н
02	П	н	Ħ	Н	н	н	Н	н
21	T	ı	Н	н	Н	н	Н	Н
00	IJ	ы	н	н	H	Н	ы	H
S1	×	H	Н	Н	Н	ı	Н	Н
80	×	H	ı	H	H	H	н	Ħ
DSL	×	×	Н	IJ	×	×	×	×
D3	×	×	×	×	×	×	ц	Н
D2	×	×	×	×	×	×	IJ	H
D1	×	×	×	×	×	×	H	H
00	×	×	×	×	×	×	니	H
DSR	×	×	×	×	Н	ы	×	×
MR	ī	Ħ	Ħ	Ħ	Ħ	Ħ	Ħ	н
CP	×	←						

X = DON'T CARE

↑ = POSTIVE GOING CLOCK PULSE

H = HIGH VOLTAGE LEVEL

74LS194 (Device No. 5) @ 80 C

CP	×	←	←	←	←	←	←	4
MR	ı	Н	н	Ħ	H	Н	Ħ	Ξ
DSR	×	×	×	×	H	ı	×	>
00	×	×	×	×	×	×	⊣	Þ
D1	×	×	×	×	×	×	IJ	Ħ
D2	×	×	×	×	×	×	ij	Ξ
D3	×	×	×	×	×	×	ы	Ξ
DST	×	×	н	П	×	×	×	>
20	×	IJ	니	IJ	н	Н	н	μ
S1	×	Ц	н	Ħ	Ц	IJ	H	Ξ
00	П	IJ	H	Ы	Щ	Ц	Н	Ħ
01	П	Н	Ц	Н	ы	H	H	Ξ
02	н	Ц	Н	Ħ	Н	П	ы	Ħ
0 3	н	H	I	H	Ħ	Н	選	Ξ

H = HIGH VOLTAGE LEVEL

L = LOW VOLTAGE LEVEL

↑ = POSTIVE GOING CLOCK PULSE

X = DON'T CARE